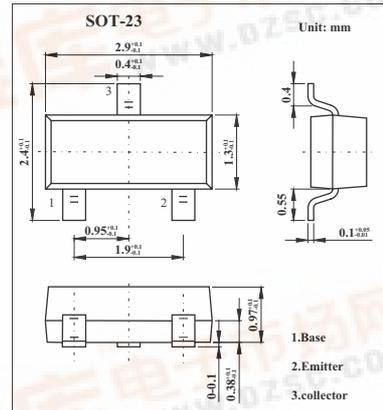


SMD Type Transistors

PNP Epitaxial Planar Silicon Transistors
2SB1295

Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Very small-sized package permitting sets to be made smaller and slimer.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-15	V
Collector-emitter voltage	V _{CEO}	-15	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-0.8	A
Collector current (pulse)	I _{CP}	-3	A
Collector dissipation	P _c	200	mW
Jumction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{cBO}	V _{CB} = -12V , I _E = 0			-100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = -4V , I _c = 0			-100	nA
DC current Gain	h _{FE}	V _{CE} = -2V , I _c = -50mA	135		600	
Gain bandwidth product	f _T	V _{CE} = -2V , I _c = -50mA		300		MHz
Output capacitance	C _{ob}	V _{CB} = -10V , f = 1MHz		15		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -5mA , I _B = -0.5mA		-10	-25	mV
	V _{CE(sat)}	I _c = -400mA , I _B = -20mA		-100	-200	mV
Base-to-emitter saturation voltage	V _{BE(sat)}	I _c = -400mA , I _B = -20mA		-0.9	-1.2	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _c = -10μA , I _E = 0	-15			V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _c = -1mA , R _{BE} = ∞	-15			V
Emitter-to-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA , I _c = 0	-5			V

hFE Classification

Marking	UL		
Rank	5	6	7
hFE	135~270	200~400	300~600

